

SANYO	No.2264B	2SB1268/2SD1904
	PNP/NPN Epitaxial Planar Silicon Transistors High-Current Switching Applications	

Applications

- . Suitable for relay drivers, high-speed inverters, converters, and other general high-current switching applications

Features

- . Suitable for sets whose height is restricted
- . Low collector to emitter saturation voltage

(): 2SB1268

Absolute Maximum Ratings at Ta=25°C

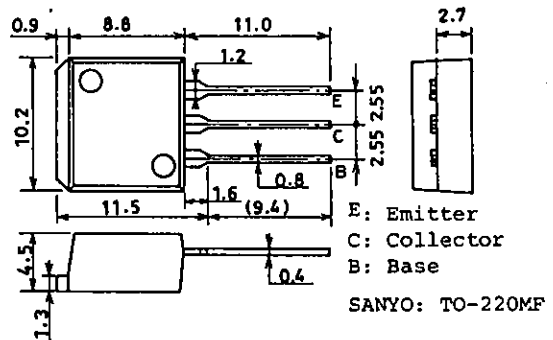
Collector to Base Voltage	V_{CB0}	(-)60	V
Collector to Emitter Voltage	V_{CE0}	(-)50	V
Emitter to Base Voltage	V_{EB0}	(-)6	V
Collector Current	I_C	(-)5	A
Peak Collector Current	i_{cp}	(-)9	A
Collector Dissipation	P_C	1.65	W
	$T_c=25^\circ C$	30	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

		min	typ	max	unit
Collector Cutoff Current	I_{CBO} $V_{CB}=(-)40V, I_E=0$			(-)0.1	mA
Emitter Cutoff Current	I_{EBO} $V_{EB}=(-)4V, I_C=0$			(-)0.1	mA
DC Current Gain	$h_{FE(1)}$ $V_{CE}=(-)2V, I_C=(-)1A$	70*		280*	
	$h_{FE(2)}$ $V_{CE}=(-)2V, I_C=(-)3A$	30			
Gain-Bandwidth Product	f_T $V_{CE}=(-)5V, I_C=(-)1A$		30		MHz
Output Capacitance	c_{ob} $V_{CB}=(-)10V, f=1MHz$		100		pF
			(160)		
C-E Saturation Voltage	$V_{CE(sat)}$ $I_C=(-)3A, I_B=(-)0.3A$			(-)0.4	V
C-B Breakdown Voltage	$V_{(BR)CBO}$ $I_C=(-)1mA, I_E=0$	(-)60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$ $I_C=(-)1mA, R_{BE}=\infty$	(-)50			V
E-B Breakdown Voltage	$V_{(BR)EBO}$ $I_E=(-)1mA, I_C=0$	(-)6			V

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Package Dimensions 2049B
(unit: mm)



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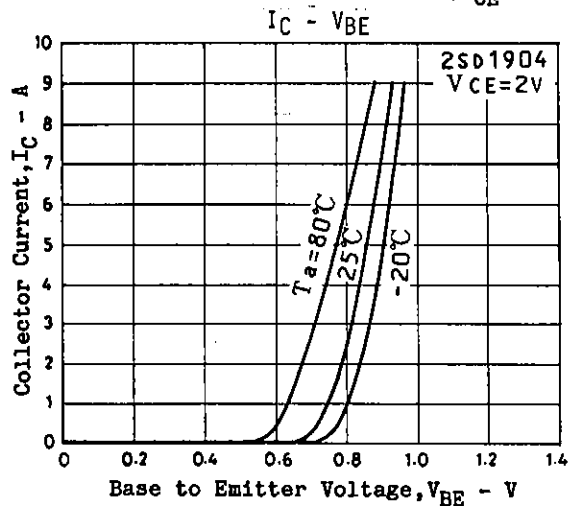
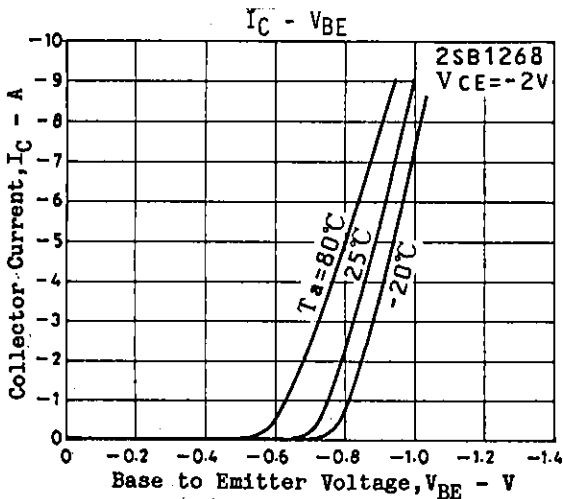
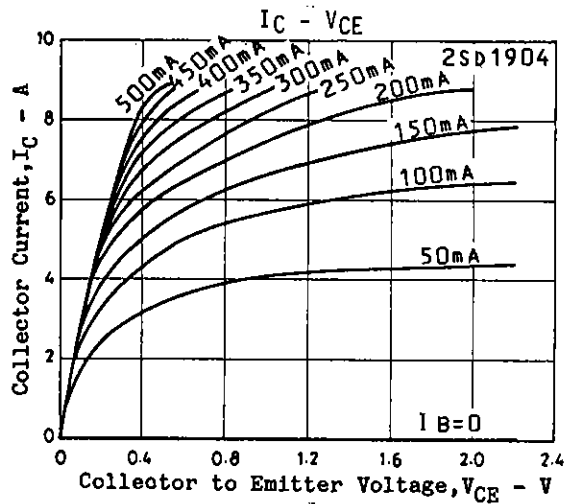
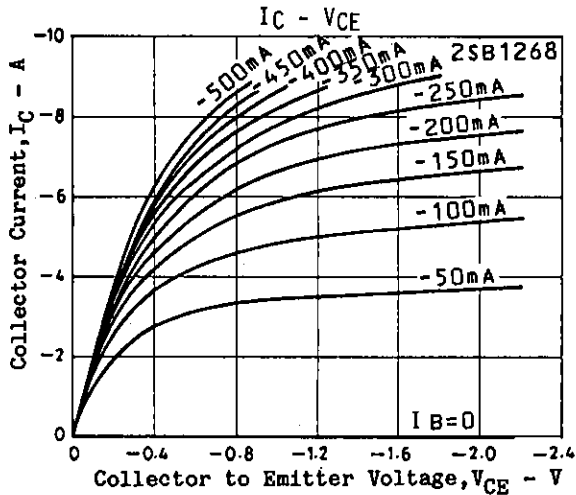
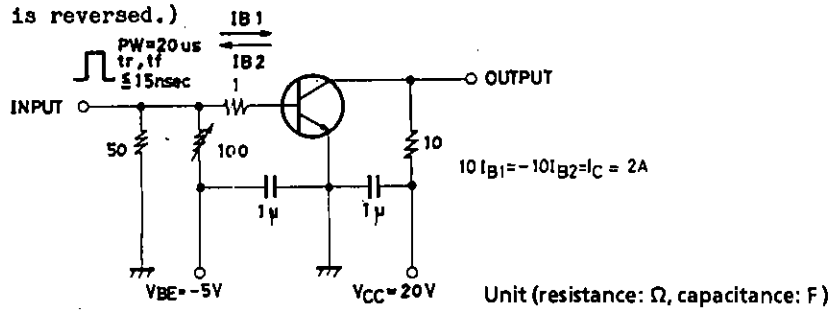
			min	typ	max	unit
Turn-on Time	t_{on}	See specified Test Circuit.		0.1		μs
Storage Time	t_{stg}	"	(0.7)	1.4		μs
Fall Time	t_f	"		0.2		μs

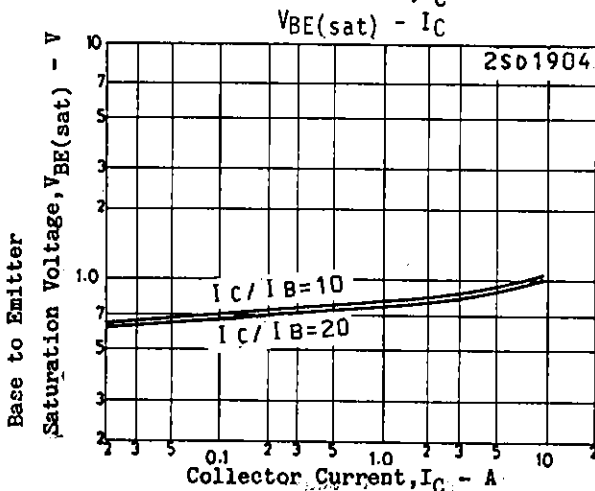
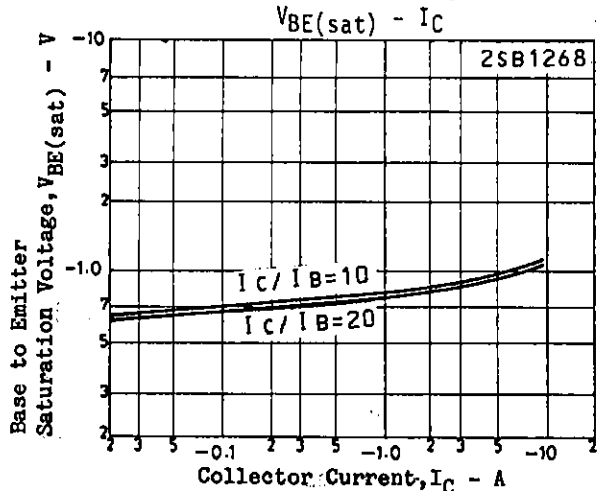
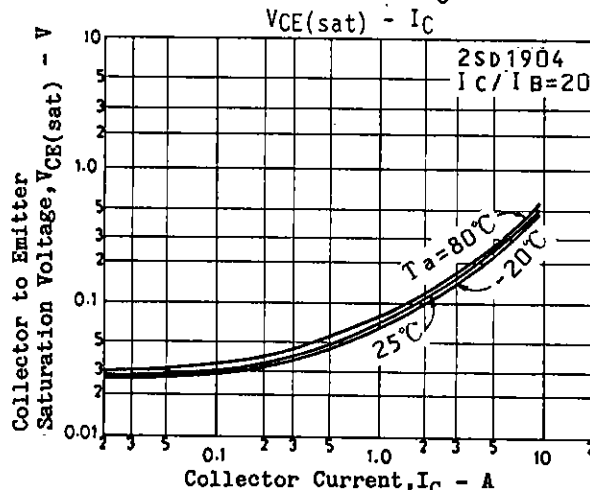
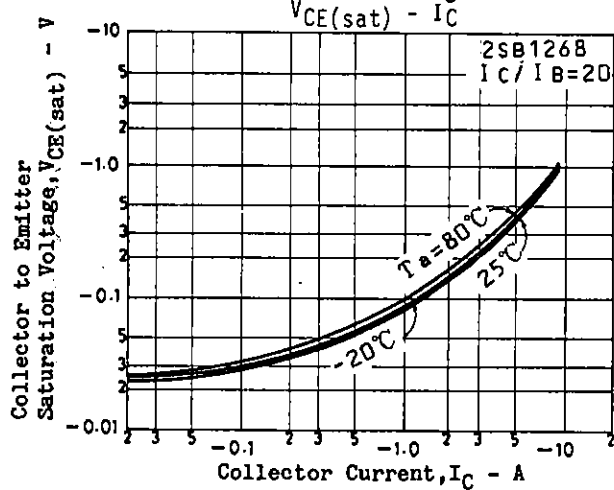
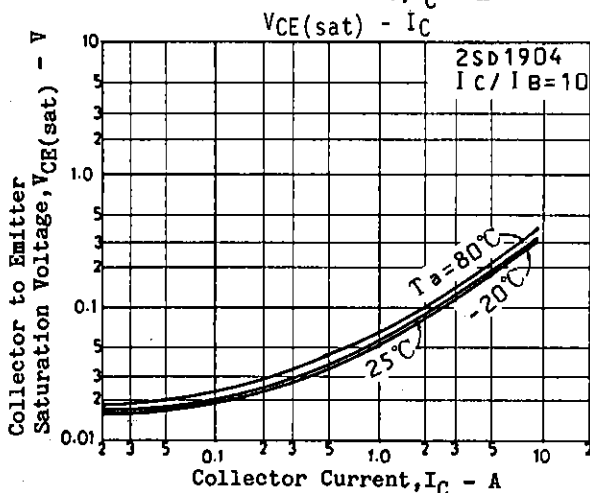
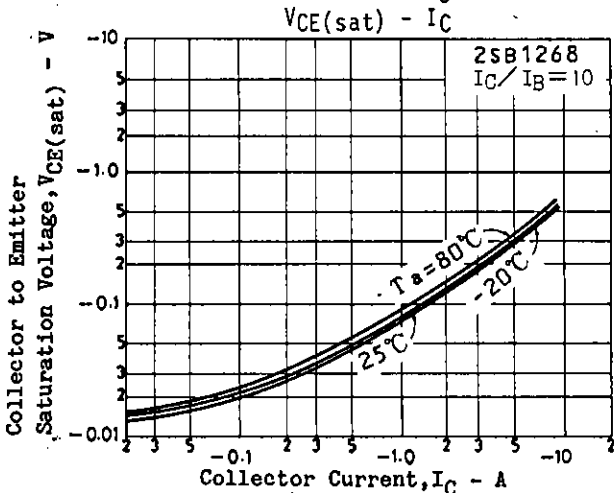
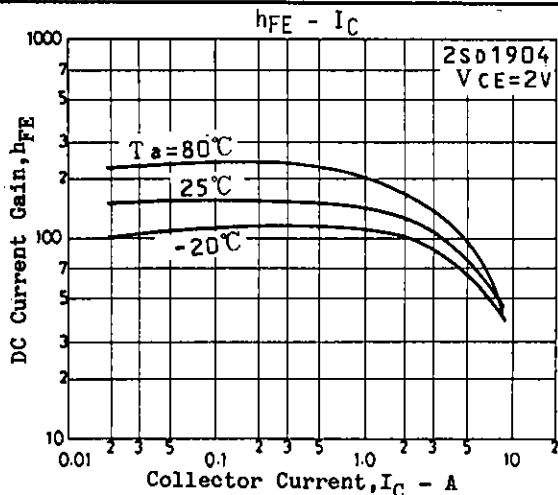
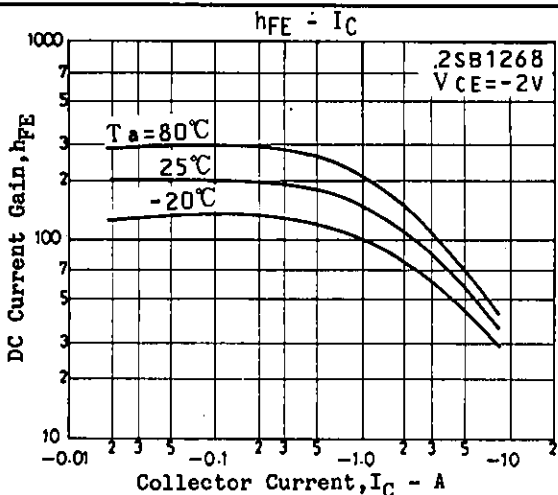
*: The 2SB1268/2SD1904 are classified by 1A h_{FE} as follows:

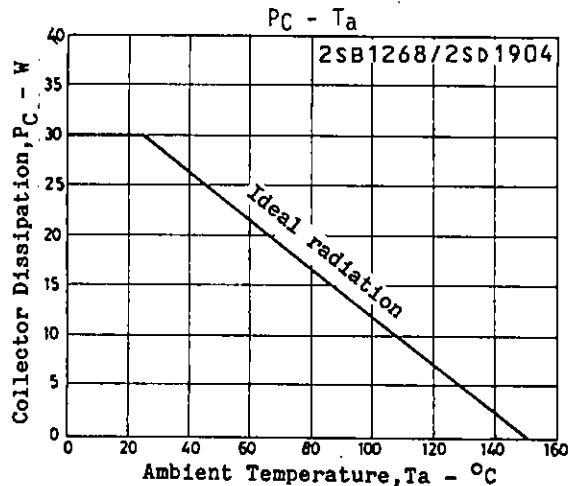
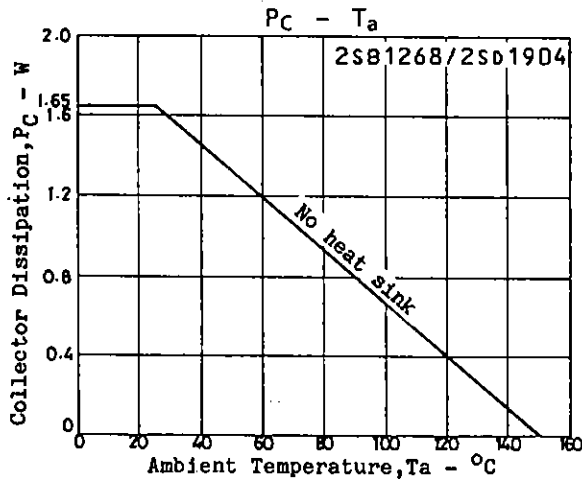
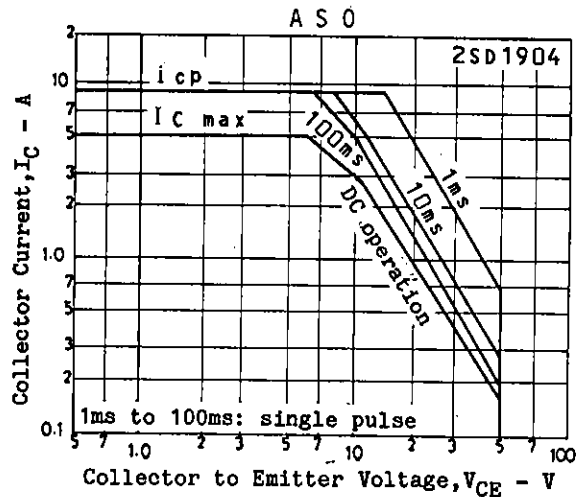
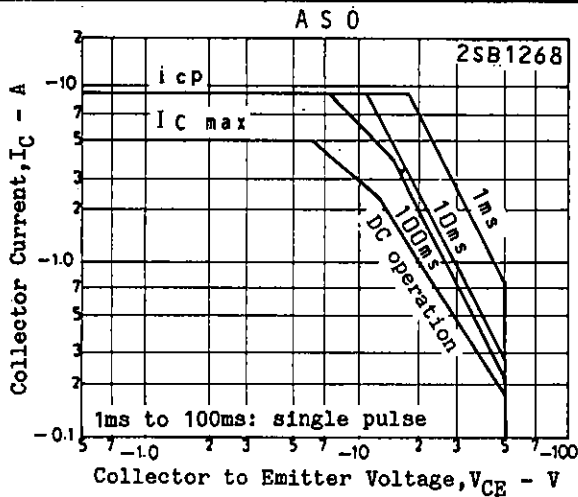
70	Q	140	100	R	200	140	S	280
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Switching Time Test Circuit

(For PNP, the polarity is reversed.)







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